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Applicant

NAKAMURA et al.

Filing Date

May 18, 2001

Group

1765

U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MS	4,437,922	03/20/1984	Bischoff et al.	—	—	—
MS	4,944,834	07/31/1990	Tada et al.	—	—	—
MS	6,036,776	03/14/2000	Kotooka et al.	—	—	—

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	Document Number	Date	Name of Patentee	Class	Subclass	Translation	
						Yes	No
	EP 0823497	02/11/1998	MEMC Electronic Materials, Inc.	—	—	X	
MS	EP 0866150	09/23/1998	Wacker Siltronic Gesellschaft fur	—	—	X	
	EP 0785298	06/26/2002	MEMC Electronic Materials, Inc.	—	—	X	
	JP 03-279290	12/10/1991	Osaka Titanium Co., Ltd.	—	—	X	
	JP 05-194076	08/03/1993	Komatsu Denshi Kinzoku KK	—	—	X	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MS	NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72
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Examiner

/Matthew Song/

Date Considered

08/09/2006

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.